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Vishay Semiconductors

## Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub>	16 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V						
$V_{TM}$	1.25 V						
I <sub>GT</sub>	45 mA						
TJ	-40 °C to 125 °C						
Package	3L TO-220AB						
Circuit configuration	Single SCR						

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

#### **DESCRIPTION**

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS	SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
Capacitive input filter $T_A = 55  ^{\circ}\text{C},  T_J = 125  ^{\circ}\text{C},  \text{common heatsink of 1 } ^{\circ}\text{C/W}$	18	22	А						

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	IETER TEST CONDITIONS VALUES								
I <sub>T(AV)</sub>	Sinusoidal waveform	16	Α						
I <sub>RMS</sub>		25	A						
V <sub>RRM</sub> /V <sub>DRM</sub>		800, 1200	V						
I <sub>TSM</sub>		320	А						
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/μs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-25TTS08-M3	800	800	10						
VS-25TTS12-M3	1200	1200	10						

# VS-25TTS08-M3, VS-25TTS12-M3

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ABSOLUTE MAXIMUM RATINGS							
DADAMETED	OVMDOL	TF0T 00	NDITIONS	VAL	UES	шито	
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	UNITS		
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° conduc	T <sub>C</sub> = 93 °C, 180° conduction half sine wave				
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	Α	
Maximum peak, one-cycle,	ı	10 ms sine pulse, rated	V <sub>RRM</sub> applied	2	70	^	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no vol	tage reapplied	3	20		
Movimum 12t for fusion	l <sup>2</sup> t	10 ms sine pulse, rated	V <sub>RRM</sub> applied	30	65	A <sup>2</sup> s	
Maximum I <sup>2</sup> t for fusing	I-I	10 ms sine pulse, no vol	515		A-S		
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10 ms, no volta	ge reapplied	51	52	A²√s	
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C		1.25		V	
On-state slope resistance	r <sub>t</sub>	T 105 °C		12.0		mΩ	
Threshold voltage	V <sub>T(TO)</sub>	- T <sub>J</sub> = 125 °C	1.0		.0	V	
Marianora	1 /1	T <sub>J</sub> = 25 °C	V Detective A/	0.5			
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	T <sub>J</sub> = 125 °C	V <sub>R</sub> = Rated V <sub>RRM</sub> /V <sub>DRM</sub>	10			
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		-	150	mA	
Maximum latching current	ΙL	Anode supply = 6 V, resi	200				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80$	T <sub>J</sub> = T <sub>J</sub> max., linear to 80 °C, V <sub>DRM</sub> = R <sub>g</sub> - k = Open				
Maximum rate of rise of turned-on current	dl/dt		15	50	A/μs		

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	w	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45	mA	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	v	
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detectively	0.25	1	
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T = 105 °C	4	μs				
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	110					



THERMAL AND MECH	THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		$T_J$ , $T_{Stg}$		-40 to +125	°C			
Maximum thermal resistance, junction to case		$R_{\text{thJC}}$	R <sub>thJC</sub> DC operation					
Maximum thermal resistance, junction to ambient		$R_{thJA}$		62	°C/W			
Typical thermal resistance, case to heatsink		$R_{\text{thCS}}$	Mounting surface, smooth and greased	0.5				
Approximate weight				2	g			
Approximate weight				0.07	oz.			
Mounting torque -	minimum			6 (5)	kgf · cm			
wounting torque -	maximum			12 (10)	(lbf · in)			
Marking davisa			Coop at do 21 TO 220AP	25TTS08				
Marking device			Case style 3L TO-220AB		25TTS12			

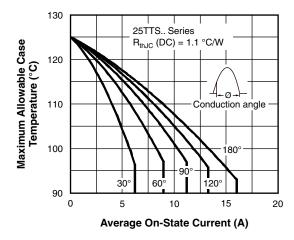


Fig. 1 - Current Rating Characteristics

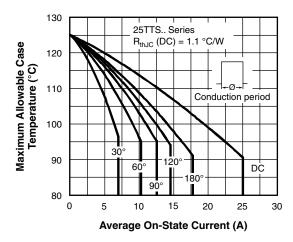


Fig. 2 - Current Rating Characteristics

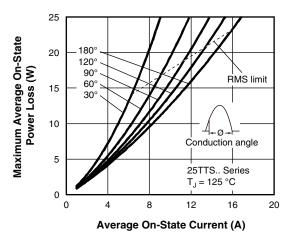


Fig. 3 - On-State Power Loss Characteristics

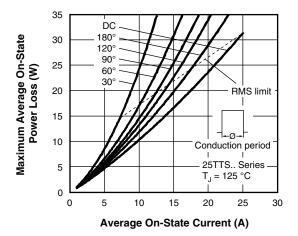
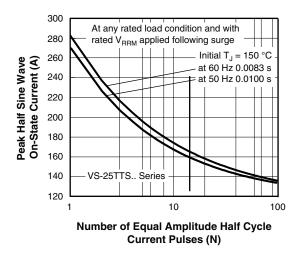


Fig. 4 - On-State Power Loss Characteristics



350 Maximum non-repetitive surge current versus pulse train duration. Control of conduction may not be maintained. 300 Peak Half Sine Wave On-State Current (A) Initial  $T_J = 150 \, ^{\circ}C$ No voltage reapplied 250 Rated V<sub>RRM</sub> reapplied 200 VS-25TTS. Series П 100 0.01 10 Pulse Train Duration (s)

Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current

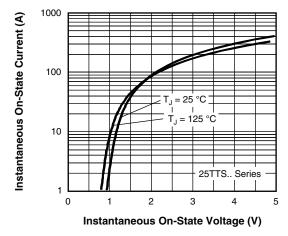


Fig. 7 - On-State Voltage Drop Characteristics

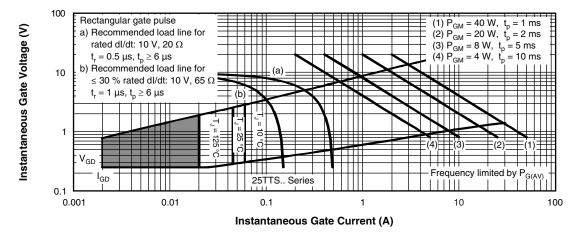


Fig. 8 - Gate Characteristics

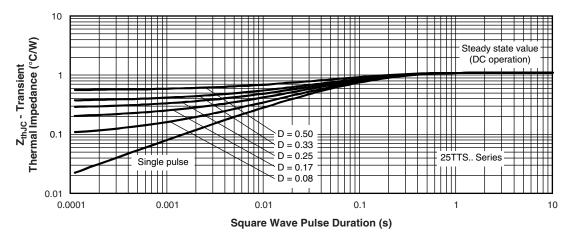
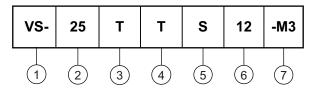


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

**2** - Current rating (25 = 25 A)

3 - Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage rating -- 08 = 800 V 12 = 1200 V

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

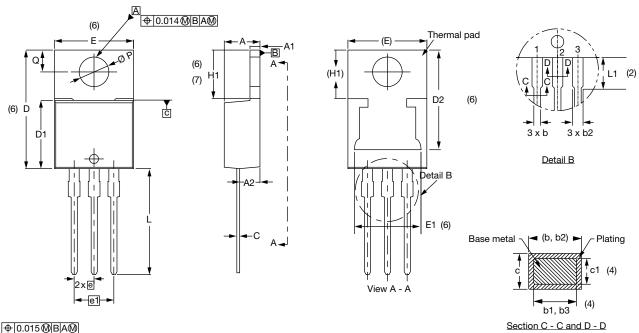
ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS08-M3	50	1000	Antistatic plastic tubes					
VS-25TTS12-M3	50	1000	Antistatic plastic tubes					

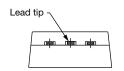
LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?96154</u>							
Part marking information	www.vishay.com/doc?95028						



### **3L TO-220AB**

### **DIMENSIONS** in millimeters and inches





Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6, 7
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								

### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2 (minimum)



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